Dual P-Channel 20-V (D-S) MOSFET

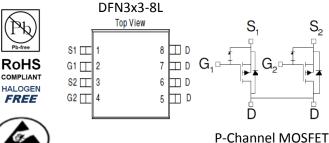
Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
	28 @ V _{GS} = -4.5V	-6.0		
-20	45 @ V _{GS} = -2.5V	-4.8		
	78 @ V _{GS} = -1.8V	-5.5		





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage			-20	V		
Gate-Source Voltage		V _{GS}	±8	V		
Continuous Danie Comment [®]	T _A =25°0	٦ ,	-6.0			
Continuous Drain Current ^a	T _A =70°0		-4.9	Α		
Pulsed Drain Current ^b		I _{DM}	-30			
Continuous Source Current (Diode Conduction) ^a		Is	-4.2	Α		
Dower Discipation 8	T _A =25°0		1.5	W		
Power Dissipation ^a	T _A =70°0		1	V V		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	35	°C/W			
Maximum Junction-to-Ambient	Steady State		81	C/VV			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

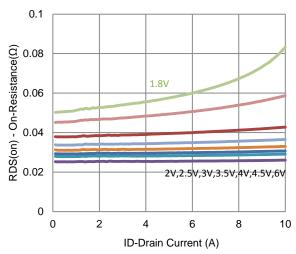
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.3			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±10	uA
Zero Gate Voltage Drain Current	1	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA
Zero Gate Voltage Brain Current	I _{DSS}	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-25	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-10			Α
		$V_{GS} = -4.5 \text{ V}, I_D = -4.8 \text{ A}$			28	
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -3.9 \text{ A}$			45	mΩ
		$V_{GS} = -1.8 \text{ V}, I_D = -3.1 \text{ A}$			78	
Forward Transconductance ^a	g _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -4.8 \text{ A}$		22		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -2.1 \text{ A}, V_{GS} = 0 \text{ V}$		-0.76		V
		Dynamic ^b				
Total Gate Charge	Q_g	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		17.8		
Gate-Source Charge	Q_{gs}	$I_{DS} = -10 \text{ V}, \text{ V}_{GS} = -4.3 \text{ V},$ $I_{D} = -4.8 \text{ A}$		3.5		nC
Gate-Drain Charge	Q_gd	1D = 4.0 K		3.3		
Turn-On Delay Time	t _{d(on)}	$V_{DS} = -10 \text{ V}, R_L = 2.1 \Omega,$		81		
Rise Time	se Time t_r			163		ns
Turn-Off Delay Time	t _{d(off)}	$I_D = -4.8 \text{ A},$ $V_{GEN} = -4.5 \text{ V}, R_{GEN} = 6 \Omega$		785		115
Fall Time	t _f	V GEN = 4.0 V, T GEN 0 12		397		
Input Capacitance	C_{iss}			683		
Output Capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		90		pF
Reverse Transfer Capacitance	C_{rss}			75		

Notes

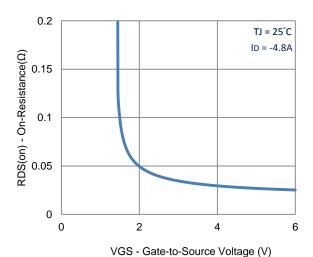
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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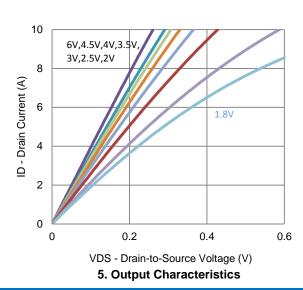
Typical Electrical Characteristics

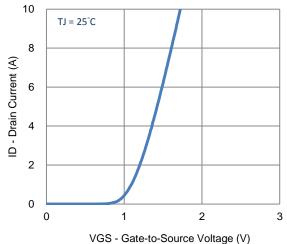


1. On-Resistance vs. Drain Current

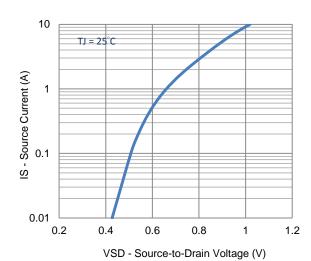


3. On-Resistance vs. Gate-to-Source Voltage

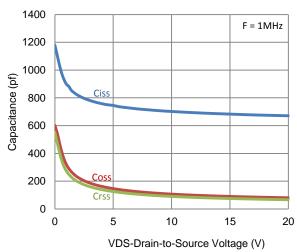




2. Transfer Characteristics

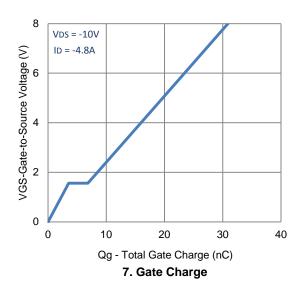


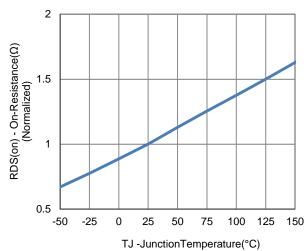
4. Drain-to-Source Forward Voltage



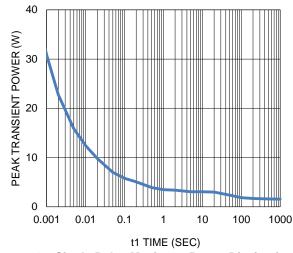
6. Capacitance

Typical Electrical Characteristics





8. Normalized On-Resistance Vs Junction Temperature

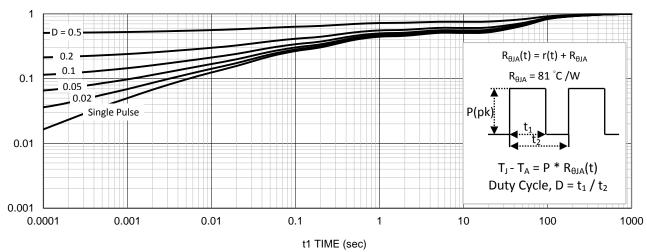


VDS Drain to Source Voltage (V)

10

9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation

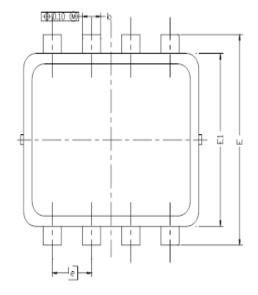


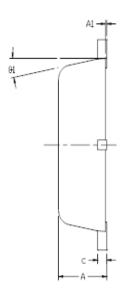
11. Normalized Thermal Transient Junction to Ambient

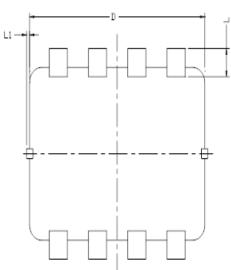
0.01

0.1

Package Information







DIM.	MILLIMETERS			INCHES			
	MIN	NDM	MAX	MIN	NDM	MAX	
Α	0.700	0.80	0,900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0,000		0.002	
b	0.24	0.30	0.35	0.009	0.012	0.014	
_	0.08	0.152	0.25	0.003	0,006	0.010	
D	2.90 BSC			0.114 BSC			
E	2.80 BSC			0.110 BSC			
E1	2.30 BSC			0.091 BSC			
9	0.65 BSC			0.026 BSC			
L	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0		0.004	
91	0	10	12	0	10	12	